

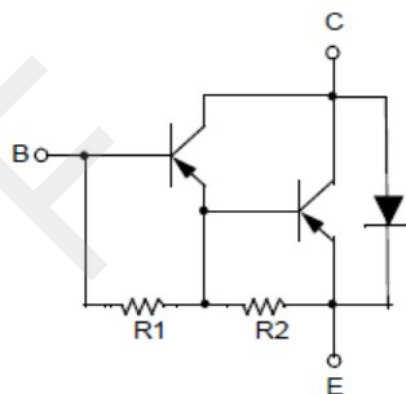
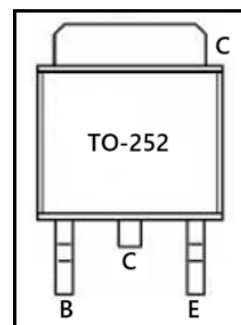
PNP Silicon Darlington Transistor MJD127

FEATURES

- High DC Current Gain
- Low Collector-Emitter Saturation Voltage
- Complementary to MJD122
- Package: TO-252

Maximum Ratings (Ta = 25°)

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-100	V
Collector-emitter voltage	V_{CEO}	-100	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-5	A
Collector Power Dissipation	P_C	1.75	W
	$P_C (T_c = 25^\circ)$	20	
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-60 ~ +150	°C



Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C = -1mA, I_E = 0$	-100			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C = -30mA, I_B = 0$	-100			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_B = -5mA, I_C = 0$	-5			V
collector-base cut-off current	I_{CBO}	$V_{CB} = -100V, I_E = 0$			-0.2	mA
collector-emitter cut-off current	I_{CEO}	$V_{CE} = -50V, I_B = 0$			-0.5	mA
emitter-base cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-2	mA
DC current gain	H_{FE}	$V_{CE} = -3V, I_C = -3A$	1000			V
		$V_{CE} = -3V, I_C = -0.5A$	1000			
collector-emitter saturation voltage	V_{CESAT1}	$I_C = -3A, I_B = -12mA$			-2	V
	V_{CESAT2}	$I_C = -5A, I_B = -20mA$			-4	
Base-Emitter On Voltage	$V_{BE(on)}$	$V_{CE} = -3V, I_C = -3A$			-2.5	V
Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 0.1MHz$			200	pF